

**Amendments to the Claims**

This listing of claims will replace all prior versions and listings of claims in the application.

**Listing of Claims:**

1. - 12. (Canceled)

13. (Currently Amended) A method for processing a semiconductor topography, comprising:

polishing the semiconductor topography with a polishing pad while simultaneously depositing a polishing solution on the polishing pad;

terminating the deposition of the polishing solution on the polishing pad;

subsequently polishing the semiconductor topography with the polishing pad having residual amounts of the polishing solution thereon; and

depositing water on the polishing pad in a plurality of dispense intervals during the step of subsequently polishing of the semiconductor topography to reduce a rate of change of a pH of the residual amounts of polishing solution on the topography polishing pad, wherein the step of depositing the water is conducted subsequent to starting the step of subsequently polishing the semiconductor topography.

14. (Original) The method of claim 13, wherein each of the plurality of dispense intervals comprise a dispense time of less than about 30 seconds.

15. (Original) The method of claim 13, wherein one or more of the plurality of dispense intervals comprise a dispense time of less than about 3 seconds.

16. (Original) The method of claim 13, wherein the polishing solution comprises slurry present on the topography prior to the polishing.

17. (Original) The method of claim 13, wherein additional polishing solution is not deposited on the polishing pad during the polishing.
18. (Original) The method of claim 13, wherein the topography comprises an upper layer of oxide formed across the topography, and wherein the oxide is substantially planar subsequent to the polishing.
19. (Previously Presented) A method for processing a semiconductor topography, comprising:
- polishing the topography with a polishing solution on a primary polishing pad during a primary polishing step without adding water to the polishing solution that is on the primary polishing pad during the polishing; and
- polishing the topography on a final polishing pad during a final polishing step, comprising depositing water on the final polishing pad in a plurality of dispense intervals to reduce a rate of change of a pH of a polishing solution on the topography.
20. (Original) The method of claim 19, further comprising transferring the topography from the primary polishing pad to the final polishing pad subsequent to the primary polishing step, wherein a substantial amount of residual slurry particles are present on the topography during the transferring.
21. (Canceled)
22. (Currently Amended) The method of claim ~~19~~, wherein a pH of the polishing solution is approximately equal to a pH of the polishing solution as commercially supplied.
23. (Currently Amended) The method of claim ~~13~~, wherein the water has a pH of about 7.
24. – 25. (Canceled)
26. (New) The method of claim 13, wherein a pH of the polishing solution on the polishing pad is substantially uniform during the step of subsequently polishing.

27. (New) The method of claim 13, wherein a pH of the polishing solution on the polishing pad varies by less than about 30 % during the step of subsequently polishing.

28. (New) The method of claim 19, wherein the step of depositing the water is conducted subsequent to starting the step of polishing the topography on the final polishing pad.

29. (New) The method of claim 19, further comprising depositing the polishing solution on the primary polishing pad during the step of polishing the topography on the primary polishing pad.

30. (New) The method of claim 19, wherein water is not added to the polishing solution before the polishing solution is deposited on the primary polishing pad.

31. (New) The method of claim 19, wherein each of the plurality of dispense intervals comprise a dispense time of less than about 30 seconds.

32. (New) The method of claim 19, wherein a pH of the polishing solution on the final polishing pad varies by less than about 2.5 during the step of polishing the topography on the final polishing pad.

33. (New) The method of claim 19, wherein subsequent to the step of polishing the topography on the primary polishing pad, a substantial amount of residual slurry particles are present on the topography.

34. (New) The method of claim 19, wherein subsequent to the step of polishing the topography on the final polishing pad, the topography is substantially free of agglomerated slurry particles.

35. (New) The method of claim 19, wherein subsequent to the step of polishing the topography on the final polishing pad, the topography is substantially free of slurry particles having a particle size greater than about 10  $\mu\text{m}$ .